

HALOGEN

FREE

HEXFRED®, Ultrafast Soft Recovery Diode, 4 A



Anode

PRODUCT SUMMARY								
Package	TO-263AB (D ² PAK)							
I _{F(AV)}	4 A							
V_{R}	600 V							
V _F at I _F	1.8 V							
t _{rr} (typ.)	17 ns							
T _J max.	150 °C							
Diode variation	Single die							

N/C

FEATURES

- Ultrafast recovery
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- Specified at operating temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- · Higher frequency operation
- · Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA04TB60S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A continuous current, the VS-HFA04TB60S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA04TB60S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V_{R}		600	V					
Maximum continuous forward current	I _F	T _C = 100 °C	4						
Single pulse forward current	I _{FSM}		25	Α					
Maximum repetitive forward current	I _{FRM}		16						
Mayira ya nayar digainatian	Ъ	T _C = 25 °C	25	W					
Maximum power dissipation	P _D	T _C = 100 °C	10	VV					
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C					





ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ	600	-	-				
Maximum forward voltage		I _F = 4.0 A		-	1.5	1.8	V		
	V _{FM}	I _F = 8.0 A	See fig. 1	-	1.8	2.2	-		
		I _F = 4.0 A, T _J = 125 °C		-	1.4	1.7			
Maximum reverse	1	V _R = V _R rated	See fig. 2	-	0.17	3.0			
leakage current	I _{RM}	$T_J = 125$ °C, $V_R = 0.8 \times V_R$ rated	See lig. 2	=	44	300	μA		
Junction capacitance	C _T	V _R = 200 V See fig. 3		-	4.0	8.0	pF		
Series inductance	L _S	Measured lead to lead 5 mm from pa	ckage body	-	8.0	-	nH		

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
_	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A}$	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		17	-			
Reverse recovery time See fig. 5, 6	t _{rr1}	T _J = 25 °C		-	28	42	ns		
occ lig. o, o	t _{rr2}	T _J = 125 °C		-	38	57			
Peak recovery current	I _{RRM1}	T _J = 25 °C	I _F = 4.0 A dI _F /dt = 200 A/μs	-	2.9	5.2	A nC		
reak recovery current	I _{RRM2}	T _J = 125 °C		-	3.7	6.7			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	40	60			
See fig. 7	Q _{rr2}	T _J = 125 °C	V _R = 200 V	-	70	105	110		
Peak rate of fall of recovery current during t _b See fig. 8	dI _{(rec)M} /dt1	T _J = 25 °C		ı	280	-	- A/µs		
	dI _{(rec)M} /dt2	T _J = 125 °C		-	235	-	Ανμδ		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R _{thJC}		-	-	5.0	K/W			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	N/VV			
Weight			-	2.0	-	g			
vveignit			-	0.07	-	oz.			
Marking device		Case style D ² PAK		HFA04	TB60S				

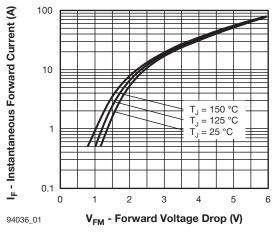


Fig. 1 - Maximum Forward Voltage Drop vs. Instantaneous Forward Current

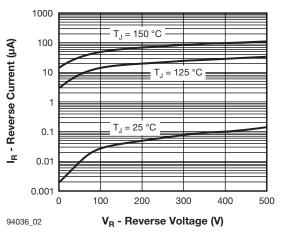


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

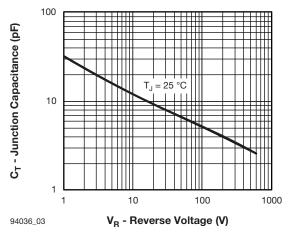


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

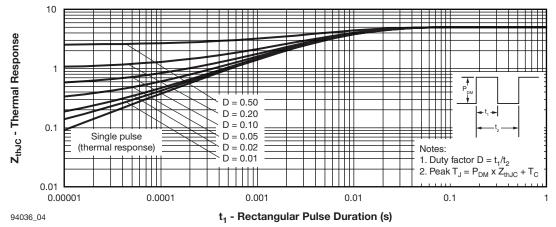


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





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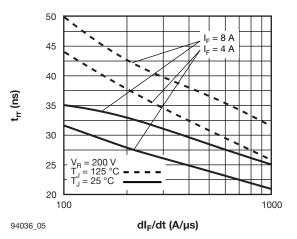


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

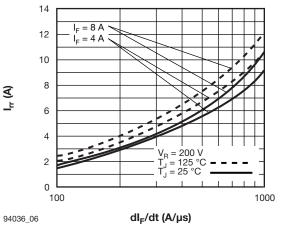


Fig. 6 - Typical Recovery Current vs. dl_F/dt

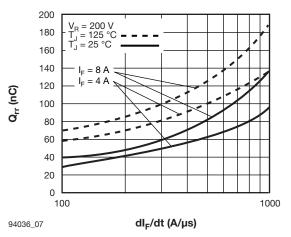


Fig. 7 - Typical Stored Charge vs. dl_F/dt

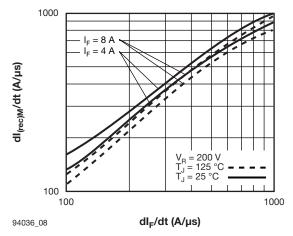


Fig. 8 - Typical dl_{(rec)M}/dt vs. dl_F/dt

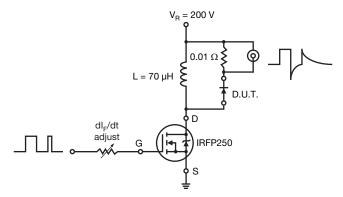
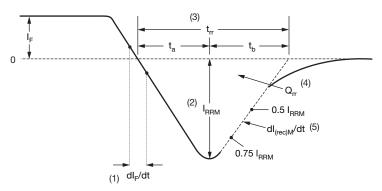


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dI_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going l_{F} to point where a line passing through 0.75 l_{RRM} and 0.50 l_{RRM} extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

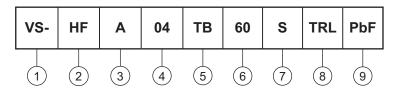
(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions



ORDERING INFORMATION TABLE

Device code



1 - HPP product suffix

2 - HEXFRED® family

Process designator: A = Electron irradiated

Current rating (04 = 4 A)

5 - Package outline (TB = TO-220, 2 leads)

6 - Voltage rating (60 = 600 V)

 $\overline{7}$ - S = D²PAK

• None = Tube (50 pieces)

• TRL = Tape and reel (left oriented)

• TRR = Tape and reel (right oriented)

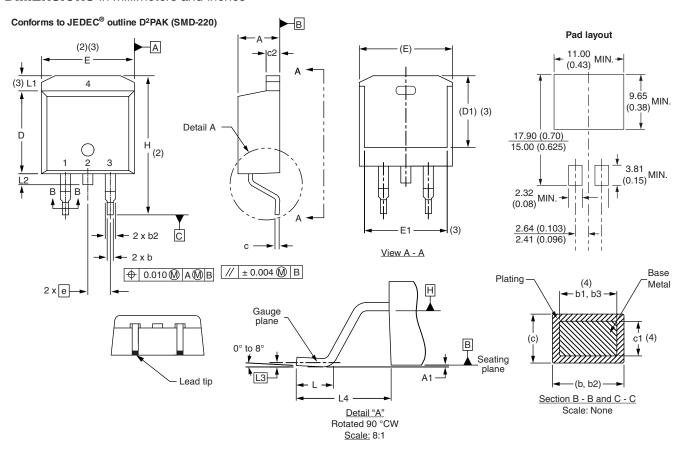
9 - PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?95046							
Part marking information	www.vishay.com/doc?95054							
Packaging information	www.vishay.com/doc?95032							



D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES		SYMBOL	MILLIM	ETERS	INC	HES	NOTES
STIVIBUL	MIN.	MAX.	MIN.	MAX.	NOTES	STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54 BSC 0.100 BSC				
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inch
- (7) Outline conforms to JEDEC® outline TO-263AB



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